



#### **DUAL N-CHANNEL ENHANCEMENT MODE MOSFET**

Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3)

Qualified to AEC-Q101 standards for High Reliability

### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> max T <sub>A</sub> = +25°C
30V	$3\Omega$ @ $V_{GS} = 4.5V$	350 mA
307	7Ω @ V <sub>GS</sub> = 2.5V	350 IIIA

### **Description**

This MOSFET has been designed to minimize the on-state resistance ( $R_{DS(ON)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

### **Applications**

- Motor Control
- Power Management Functions

**Ordering Information** (Note 4)

- DC-DC Converters
- Backlighting

#### Terminal Connections: See Diagram

 Terminals: Finish – Matte Tin annealed over Copper leadframe Solderable per MIL-STD-202, Method 208 <sup>3</sup>

Case Material: Molded Plastic, "Green" Molding Compound UL

Weight: 0.006 grams (approximate)

Flammability Classification Rating 94V-0

Moisture Sensitivity: Level 1 per J-STD-020

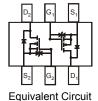
Low On-Resistance
Low Input Capacitance
Fast Switching Speed
ESD Protected Gate to 2kV

**Mechanical Data** 

Case: SOT563







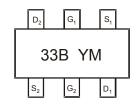
Top View

Part Number	Case	Packaging
DMN33D8LV-7	SOT563	3K/Tape & Reel
DMN33D8LV-13	SOT563	10K/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**



33B = Product Type Marking Code YM = Date Code Marking Y = Year ex: V = 2008 M = Month ex: 9 = September

Date Code Key

Year	201	1	2012		2013	20	14	2015		2016	2	2017
Code	Υ		Z		Α	[	3	С		D		E
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Drain-Source Voltage			$V_{DSS}$	30	V
Gate-Source Voltage	$V_{GSS}$	±20	V		
Continuous Drain Current (Note 5) $V_{GS} = 4.5V$ Steady $T_A = +25^{\circ}C$ State $T_A = +70^{\circ}C$			I <sub>D</sub>	350 200	mA
Maximum Continuous Body Diode Forward Current	(Note 5)	Is	0.5	Α	
Pulsed Drain Current (10µs pulse, duty cycle=1%)		I <sub>DM</sub>	0.8	Α	

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units	
Total Dayer Dissipation (Note 5)	T <sub>A</sub> = +25°C	0	0.43	- W	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +70°C	$P_{D}$	0.20		
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	288	°C/W		
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to 150	°C		

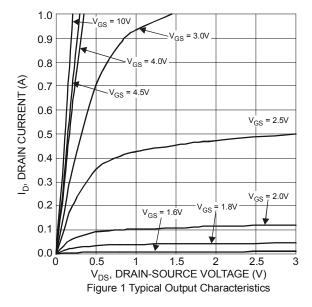
# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

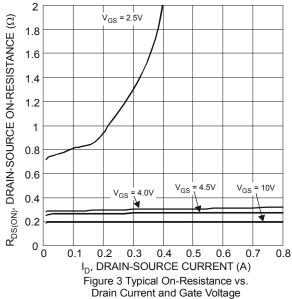
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
DFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$
Zero Gate Voltage Drain Current @T <sub>C</sub> = +2	25°C I <sub>DSS</sub>	_	_	1	μΑ	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	V <sub>GS</sub> = ±16V, V <sub>DS</sub> = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V <sub>GS(th)</sub>	8.0	_	1.5	V	$V_{DS} = 3V, I_{D} = 100\mu A$
		_	_	2.4		$V_{GS} = 10V, I_D = 250mA$
Static Drain-Source On-Resistance		_	_	3.0	Ω	$V_{GS}$ = 4.5V, $I_{D}$ = 250mA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	_	5.0	1 12	$V_{GS} = 4.0V, I_D = 10mA$
		_	_	7.0		$V_{GS} = 2.5V, I_D = 10mA$
Forward Transfer Admittance	Y <sub>fs</sub>	10	_	-	mS	$V_{DS} = 3V, I_{D} = 10mA$
Diode Forward Voltage		_	_	1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = 115mA
DYNAMIC CHARACTERISTICS (Note 7)	•					
Input Capacitance		_	48	_	pF	., 51, 14
Output Capacitance	C <sub>oss</sub>	_	11	_	pF	$V_{DS} = 5V, V_{GS} = 0V,$ -f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	8	_	pF	1 - 1.01/11/2
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg	_	0.55	_	nC	
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	1.23	_	nC	$V_{GS} = 10V, V_{DS} = 10V,$
Gate-Source Charge	Qgs	_	0.14	_	nC	I <sub>D</sub> = 250mA
Gate-Drain Charge	Q <sub>gd</sub>	_	0.14	_	nC	
Turn-On Delay Time		_	2.9	_	ns	
Turn-On Rise Time		_	2.6	_	ns	V <sub>DD</sub> = 30V, V <sub>GS</sub> = 10V,
Turn-Off Delay Time		_	18.2	_	ns	$R_G = 25\Omega$ , $I_D = 200 \text{mA}$
Turn-Off Fall Time		_	13.6	_	ns	

5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to product testing.







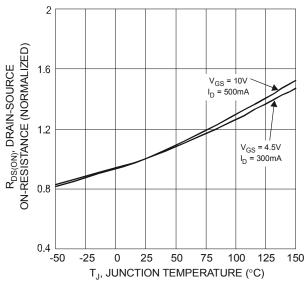
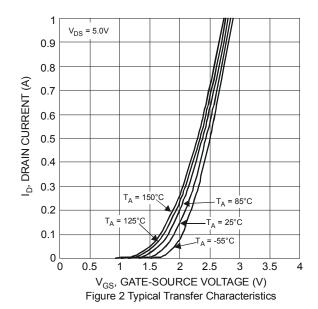
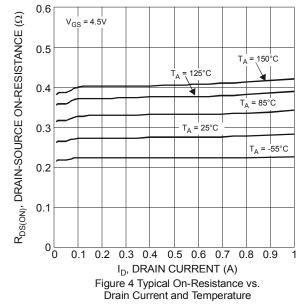
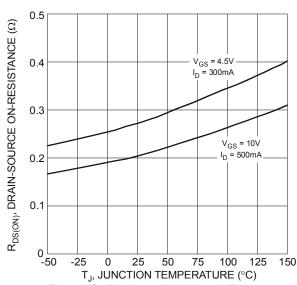


Figure 5 On-Resistance Variation with Temperature









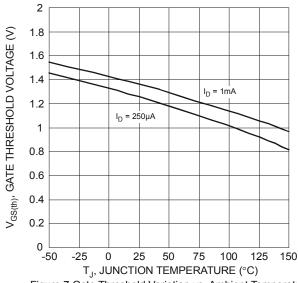
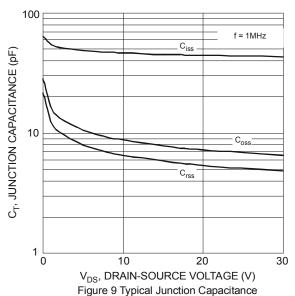
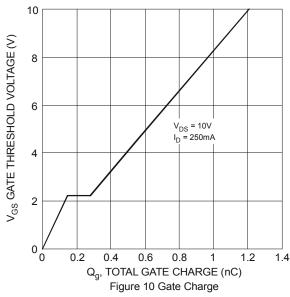


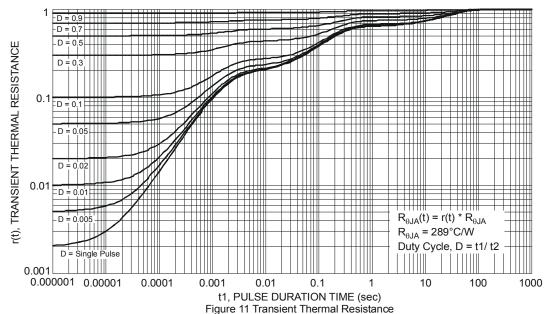
Figure 7 Gate Threshold Variation vs. Ambient Temperature



0.9 0.8 I<sub>S</sub>, SOURCE CURRENT (A) 0.7 0.6 T<sub>A</sub> = 150°C 0.5 0.4 0.3 0.2  $T_A = -55^{\circ}C$ 0.1 0 0 0.3 0.6 0.9 1.2 1.5 V<sub>SD</sub>, SOURCE-DRAIN VOLTAGE (V) Figure 8 Diode Forward Voltage vs. Current

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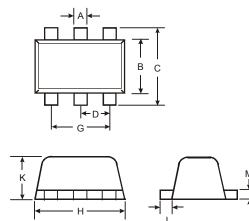






# Package Outline Dimensions

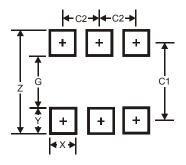
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT563							
Dim	Min	Max	Тур				
Α	0.15	0.30	0.20				
В	1.10	1.25	1.20				
С	1.55	1.70	1.60				
D	-	-	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
K	<b>K</b> 0.55 0.60 0.60						
L	0.10	0.30	0.20				
М	0.10	0.18	0.11				
All	All Dimensions in mm						

## **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Z	2.2
G	1.2
Х	0.375
Y	0.5
C1	1.7
C2	0.5



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